

# EPIGAP Optronik GmbH

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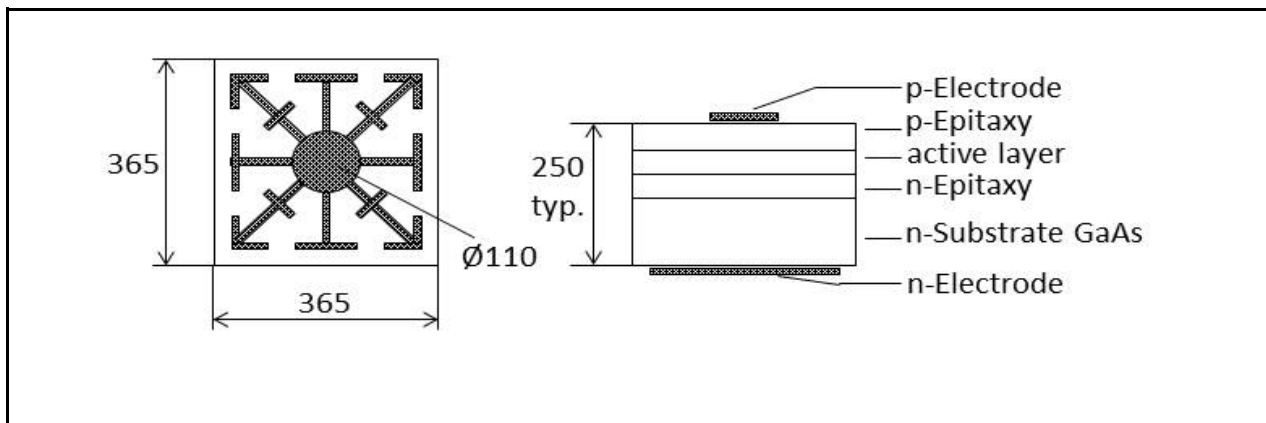
## Data Sheet

### LED Chip Infrared

**EOLC-1020-17**

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	MQW / GaAs	P (anode) up



### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.25	1.45	V
Reverse current	$I_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Output power*	$I_F = 20 \text{ mA}$	$\Phi_e$		3		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$		1020		nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching times	$I_F = 20 \text{ mA}$	$t_r, t_f$		15; 20		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 028



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.